Abstracts

A 2-W Ku-Band Monolithic GaAs FET Amplifier

H.M. Macksey, H.Q. Tserng and H.D. Shih. "A 2-W Ku-Band Monolithic GaAs FET Amplifier." 1985 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 85.1 (1985 [MCS]): 27-30.

A monolithic three-stage Ku-band GaAs FET power amplifier has been designed, fabricated. Epitaxial layers are grown by molecular beam epitaxy FETs have a source overlay geometry with the n+ ledge channel structure. The amplifiers have up to 2 W output power at 16.5 GHz with 12 dB gain, 20% efficiency.

❑ Return to main document.

Click on title for a complete paper.